

FORM PTO-1449

Atty. Docket No.:
B784.312-1Application No.:
10/017,734LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION
DISCLOSURE STATEMENTFirst Named Inventor:
Baowei KANGFiling Date:
December 18, 2001Group Art:
2823

U.S. PATENT DOCUMENTS

Examiner Initials	Document No.	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Documents
AA			
AB			
AC			
AD			
AE			
AF			
AG			

FOREIGN PATENT DOCUMENTS

	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Documents	Translation Yes No
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AI				

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

KN	AJ	Zohta, Yasuhito et al., "Shallow Donor State Produced by Proton Bombardment of Silicon", <i>Japan J. Appl. Phys.</i> 10, 1971, 532-533.
KN	AK	Gorelkinskii, Yu and Nevinnyui, N.N., "Reversible Transformation of Defects in Hydrogen-Implanted Silicon", <i>Nuclear Instruments and Methods</i> 209/210, 1983, 677-682.
KN	AL	Ntsoenzok, E. et al., "Study of the Defects Induced in N-Type Silicon Irradiated by 1-3 MeV Protons", <i>IEEE Transactions of Nuclear Science</i> , Vol. 41, No. 6, December 1994, 1932-1936.
KN	AM	Ntsoenzok, E. et al., "Evolution of Shallow Donors with Proton Fluence in N-Type Silicon", <i>J. appl. Phys.</i> 79(11), June 1, 1996, 8274-8277.
KN	AN	S. Godey et al., "Effect of Shallow Donors Induced by Hydrogen on P+N Junctions", <i>Materials Science & Engineering B58</i> , 1999, 108-112.

EXAMINER:

K. H. M. M. M. M.

DATE CONSIDERED:

06/10/04

EXAMINER: Initial if citation considered whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.